



SANYO Semiconductors

DATA SHEET

2SC5980

NPN Epitaxial Planar Silicon Transistor

High-Current Switching Applications

Applications

- DC / DC converter, relay drivers, lamp drivers, motor drivers, flash.

Features

- Adoption of FBET, MBIT process.
- High current capacitance.
- Low collector-to-emitter saturation voltage.
- High-speed switching.
- Narrow h_{FE} width.
- High allowable power dissipation.

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		100	V
Collector-to-Emitter Voltage	V_{CES}		100	V
Collector-to-Emitter Voltage	V_{CEO}		50	V
Emitter-to-Base Voltage	V_{EBO}		6	V
Collector Current	I_C		8	A
Collector Current (Pulse)	I_{CP}		11	A
Base Current	I_B		2	A
Collector Dissipation	P_C		1.0	W
		$T_c=25^\circ\text{C}$	15	W
Junction Temperature	T_J		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=40\text{V}, I_E=0$			0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=2\text{V}, I_C=500\text{mA}$	250		400	

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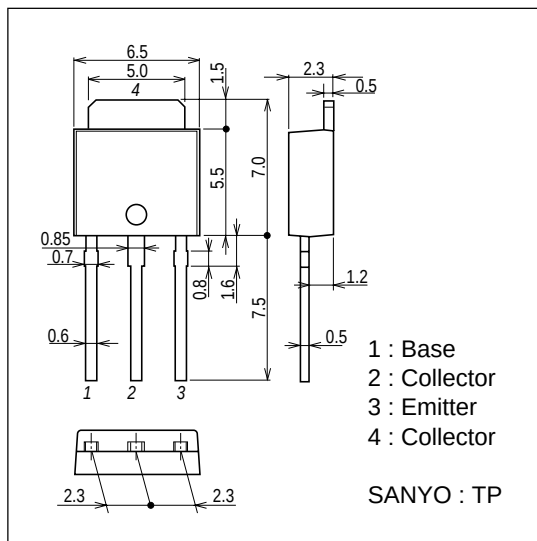
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Gain-Bandwidth Product	f_T	$V_{CE}=10V, I_C=500mA$		330		MHz
Output Capacitance	C_{ob}	$V_{CB}=10V, f=1MHz$		28		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=3.5A, I_B=175mA$		125	190	mV
		$I_C=2A, I_B=40mA$		100	150	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=2A, I_B=40mA$		0.83	1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C=100\mu A, R_{BE}=\infty$	100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, R_{BE}=\infty$	50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6			V
Turn-ON Time	t_{on}	See specified Test Circuit.		30		ns
Storage Time	t_{stg}	See specified Test Circuit.		420		ns
Fall Time	t_f	See specified Test Circuit.		25		ns

Package Dimensions

unit : mm

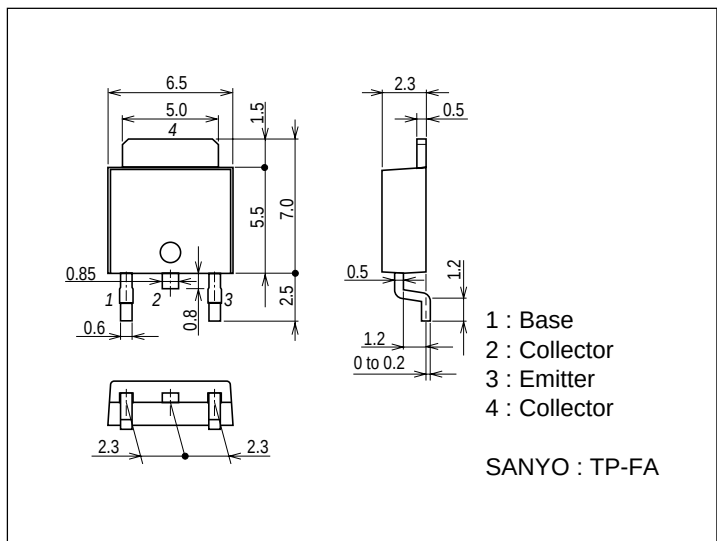
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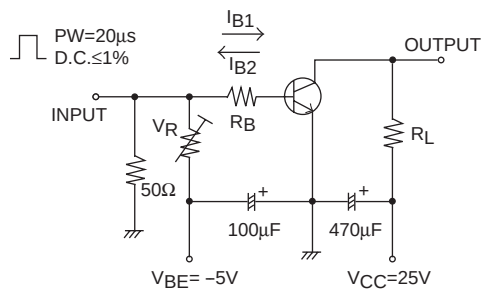
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unit : mm

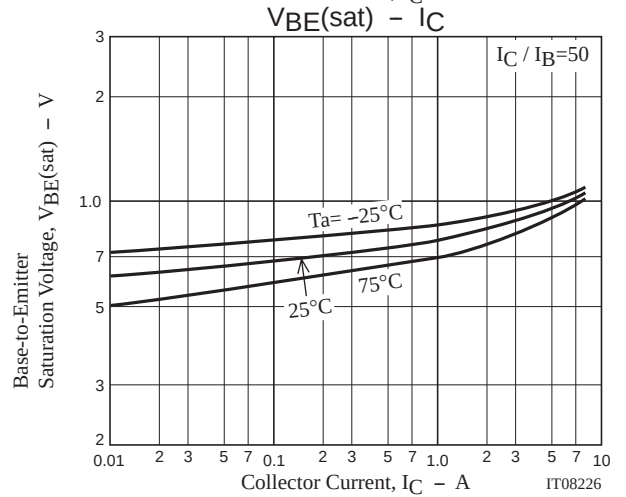
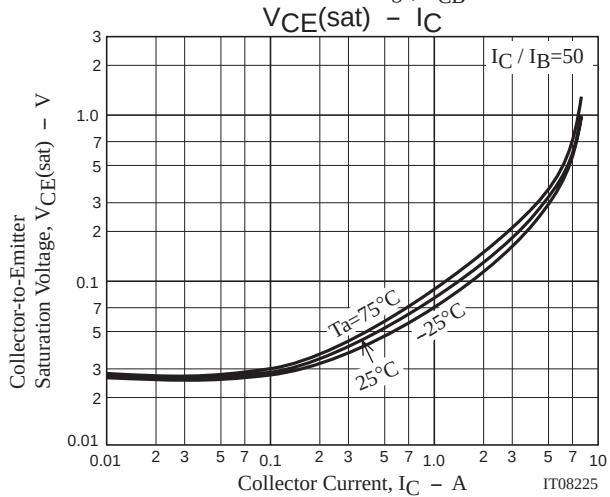
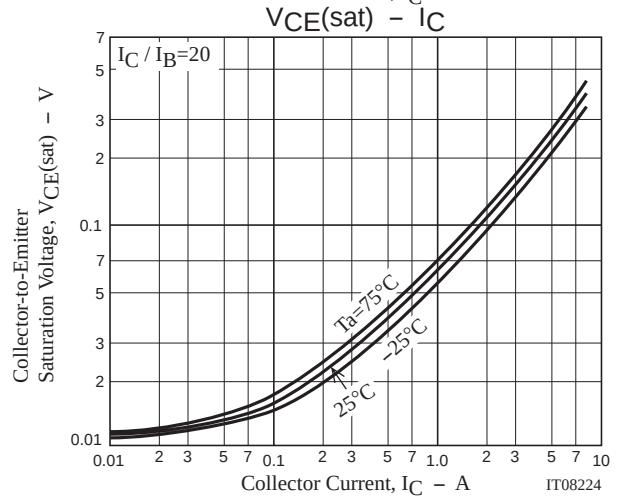
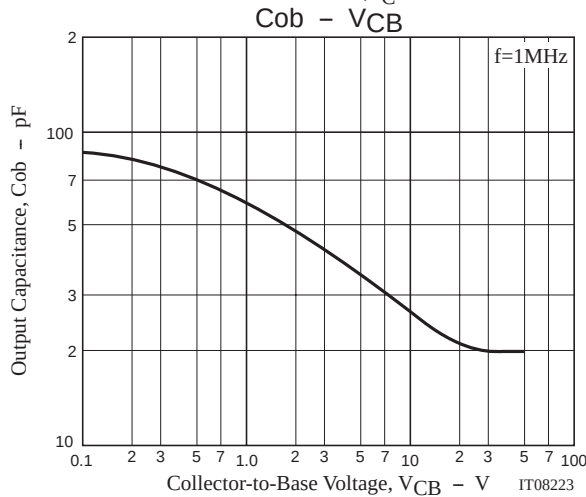
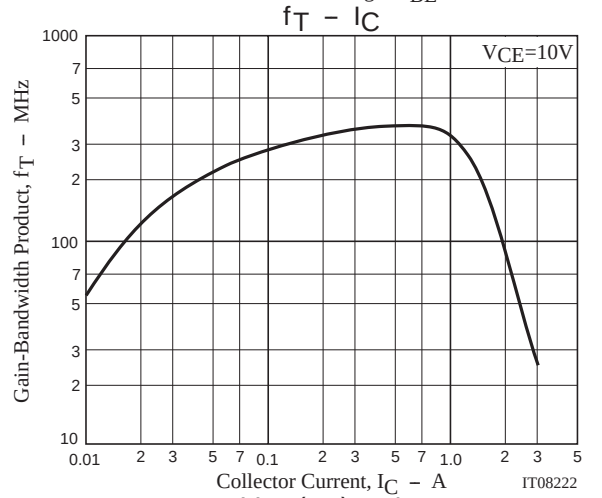
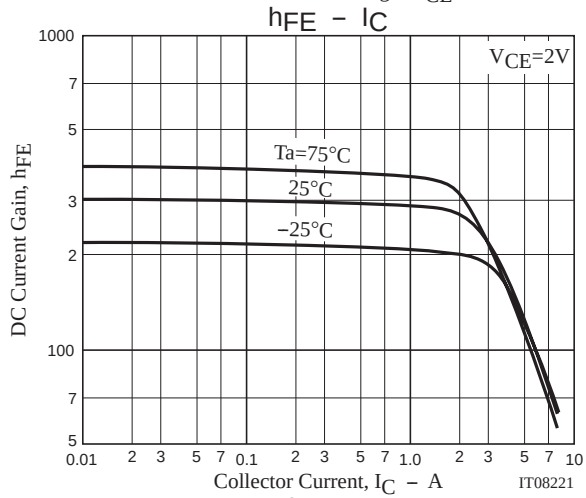
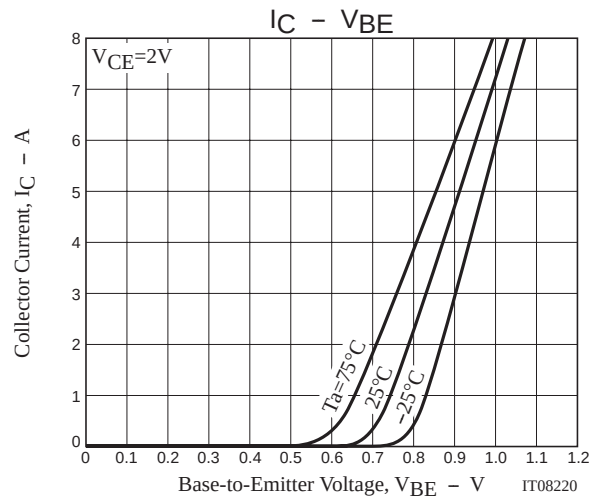
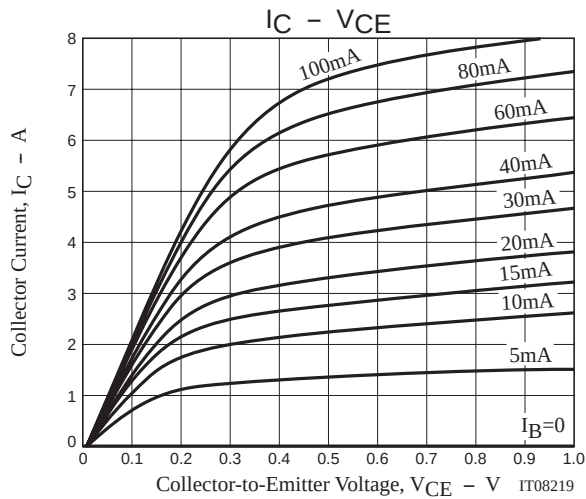
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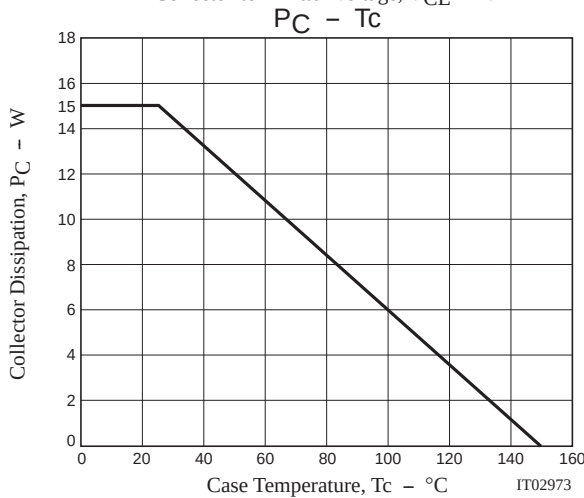
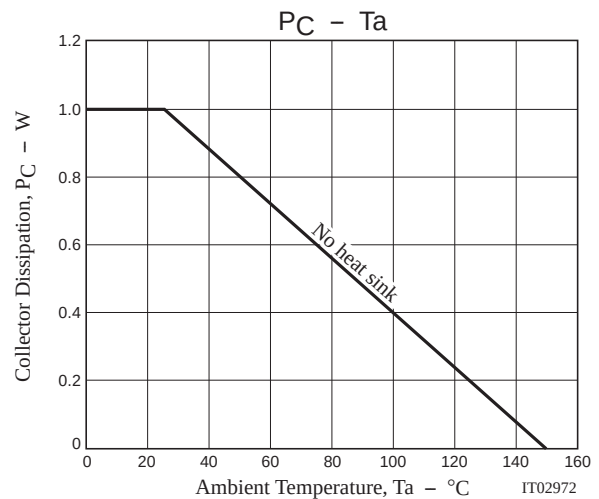
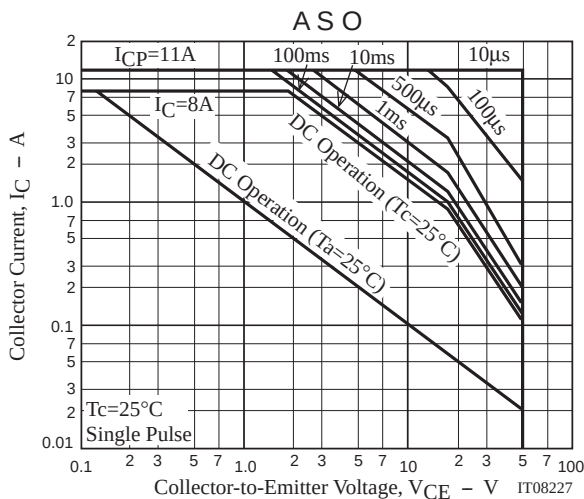


Switching Time Test Circuit



$$I_C = 20I_{B1} = -20I_{B2} = 2.5A$$





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